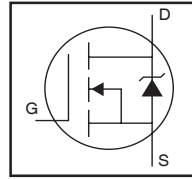


# AUIRLR2703

HEXFET® Power MOSFET

- Advanced Planar Technology
- Logic-Level Gate Drive
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified\*



$V_{(BR)DSS}$		<b>30V</b>
$R_{DS(on)}$ max.		<b>45mΩ</b>
$I_D$ (Silicon Limited)		<b>23A</b>
$I_D$ (Package Limited)		<b>20A</b>

## Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	23	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	16	
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Package Limited)	20	
$I_{DM}$	Pulsed Drain Current ①	96	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	45	W
	Linear Derating Factor	0.30	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 16	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited)②	77	mJ
$E_{AS}(\text{tested})$	Single Pulse Avalanche Energy Tested Value ⑥	200	
$I_{AR}$	Avalanche Current ①	14	A
$E_{AR}$	Repetitive Avalanche Energy ①	4.5	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	3.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ⑦	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at <http://www.irf.com/>

### Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.030	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.045	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 14A ④
		—	—	0.065		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	6.4	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 14A ⑦
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -16V

### Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>n</sub>	Total Gate Charge	—	—	15	nC	I <sub>D</sub> = 14A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	4.6		V <sub>DS</sub> = 24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	9.3		V <sub>GS</sub> = 4.5V ④⑦
t <sub>d(on)</sub>	Turn-On Delay Time	—	8.5	—	ns	V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	140	—		I <sub>D</sub> = 14A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	12	—		R <sub>G</sub> = 12Ω
t <sub>f</sub>	Fall Time	—	20	—		V <sub>GS</sub> = 4.5V, R <sub>D</sub> = 1.1Ω ④⑦
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—		nH
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	450	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	210	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	110	—		f = 1.0MHz ⑦

### Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	23⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	96		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 14A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	65	97	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 14A
Q <sub>rr</sub>	Reverse Recovery Charge	—	140	210	nC	di/dt = 100A/μs ④⑦
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

#### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② V<sub>DD</sub> = 15V, starting T<sub>J</sub> = 25°C, L = 570μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 14A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 14A, di/dt ≤ 140A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L<sub>S</sub> of D-PAK is measured between lead and center of die contact.
- ⑦ Uses IRL2703 data and test conditions.

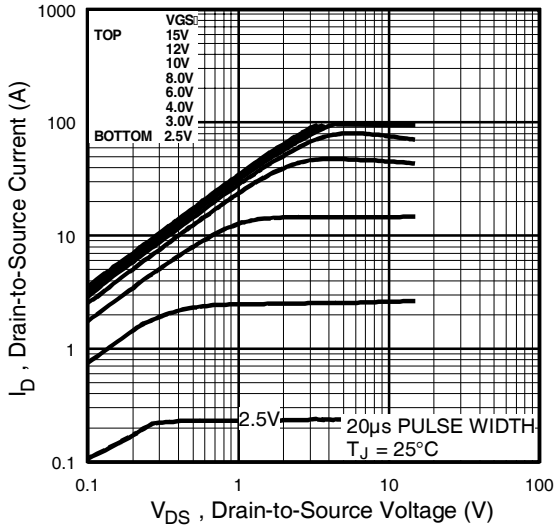
**Qualification Information<sup>†</sup>**

<b>Qualification Level</b>		Automotive (per AEC-Q101) <sup>††</sup>	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		D-PAK	MSL1
<b>ESD</b>	Machine Model	Class M2 (+/- 150V) <sup>†††</sup> AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V) <sup>†††</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>†††</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

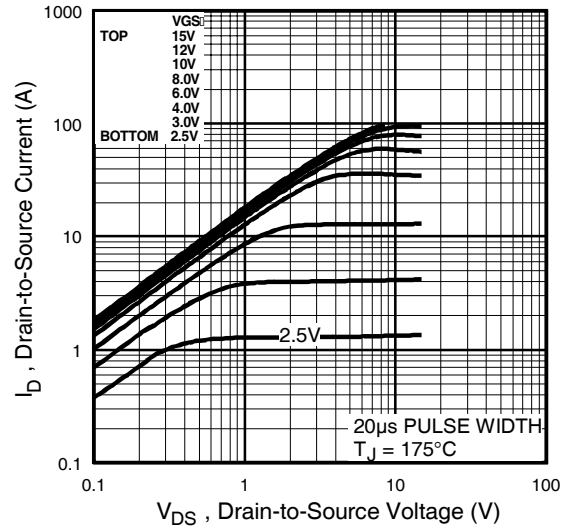
† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

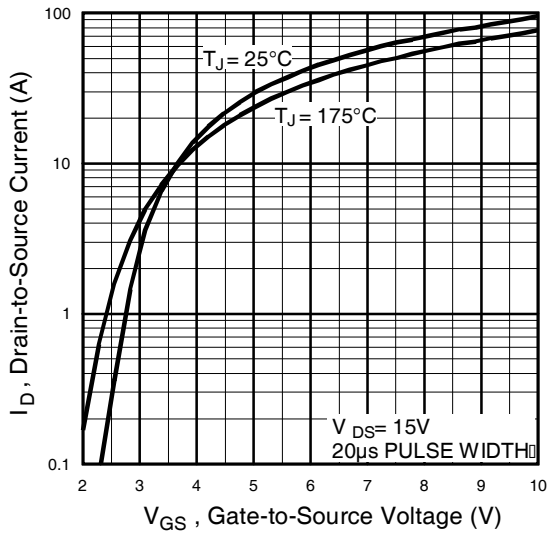
††† Highest passing voltage



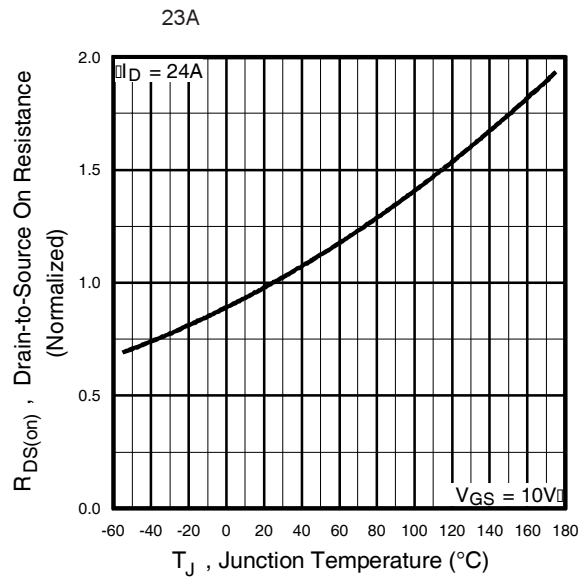
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



**Fig 3.** Typical Transfer Characteristics



**Fig 4.** Normalized On-Resistance Vs. Temperature

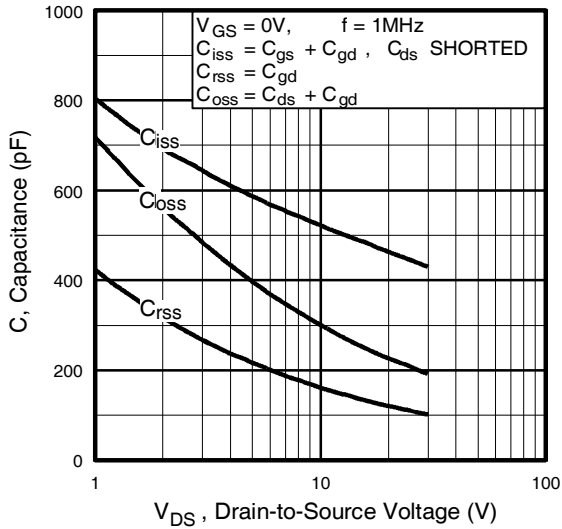


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

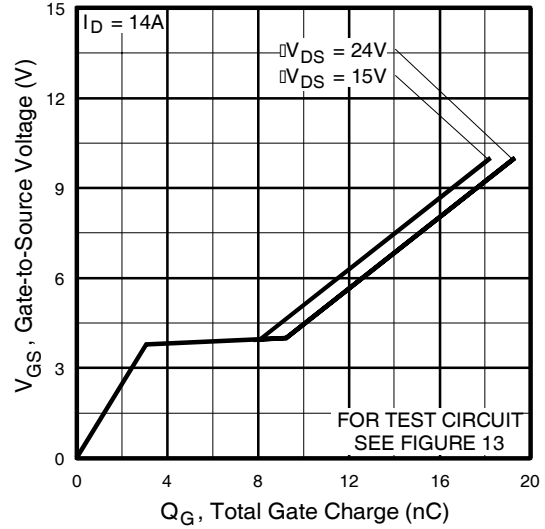


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

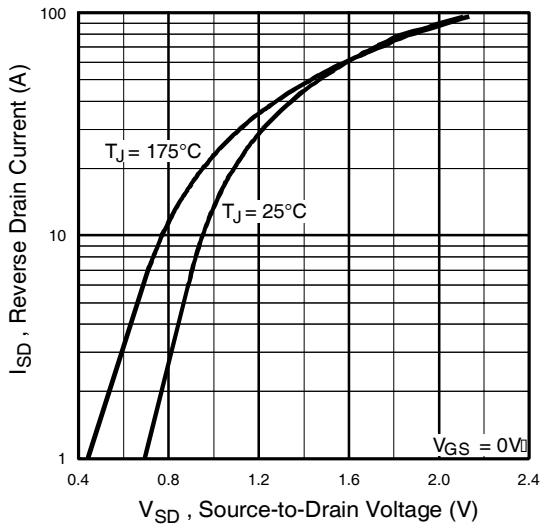


Fig 7. Typical Source-Drain Diode Forward Voltage

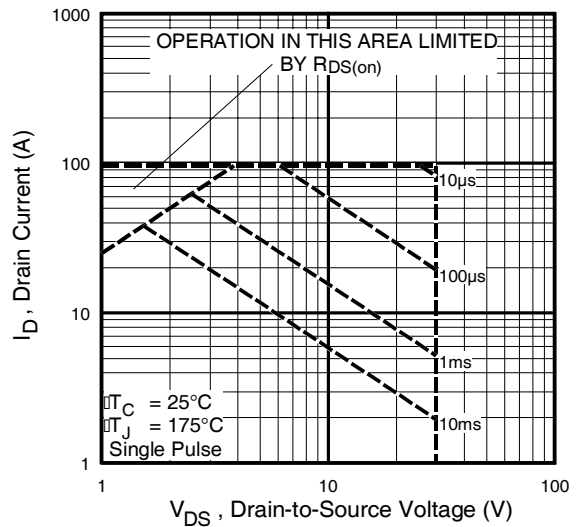
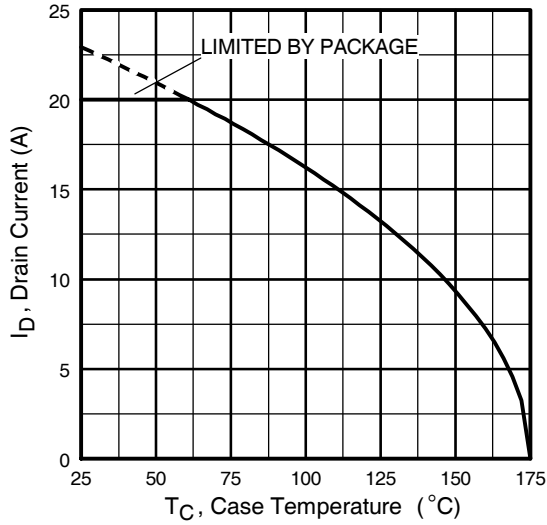
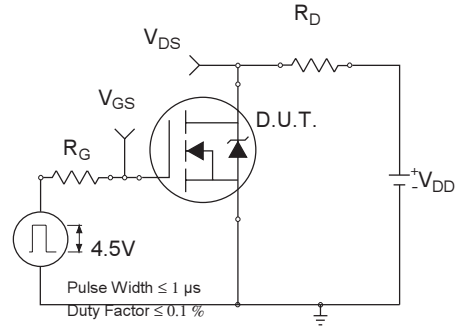


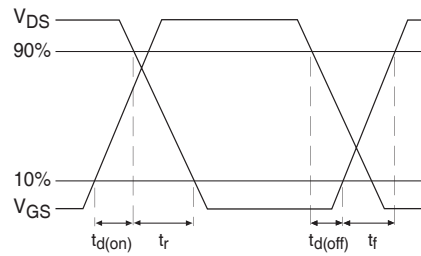
Fig 8. Maximum Safe Operating Area



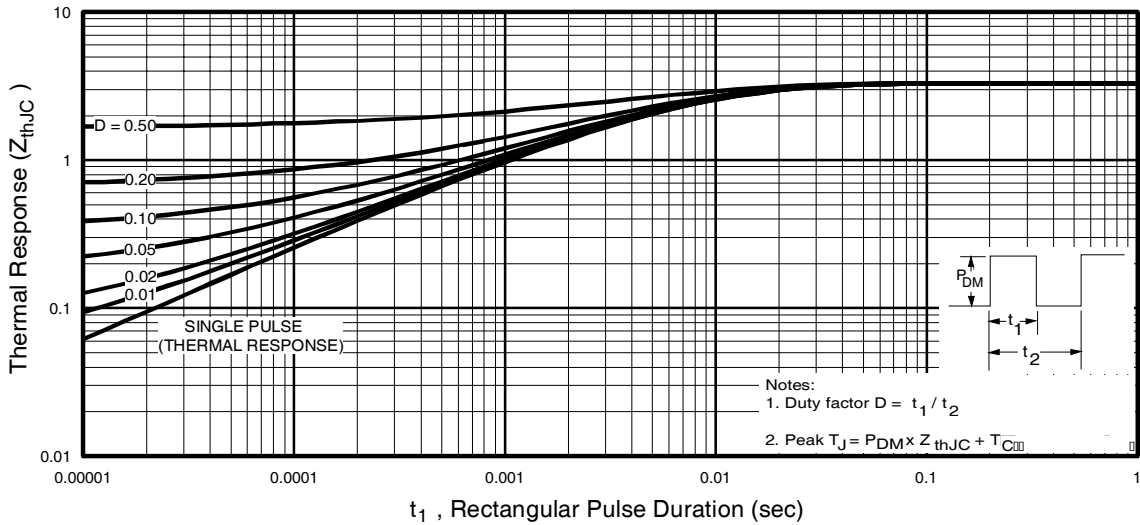
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

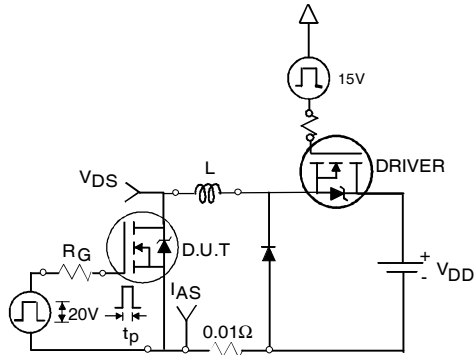


Fig 12a. Unclamped Inductive Test Circuit

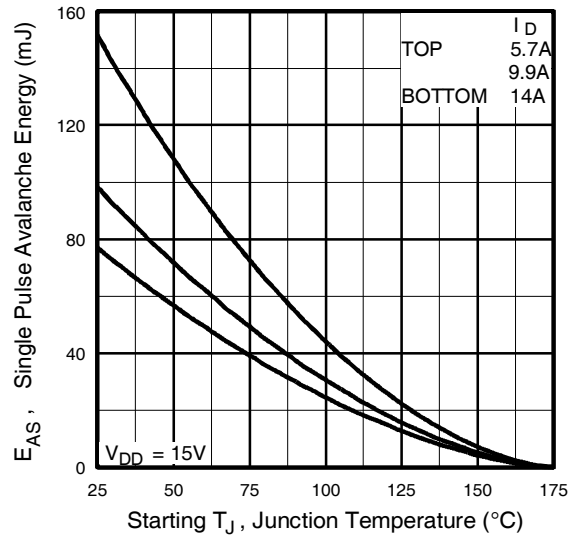


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

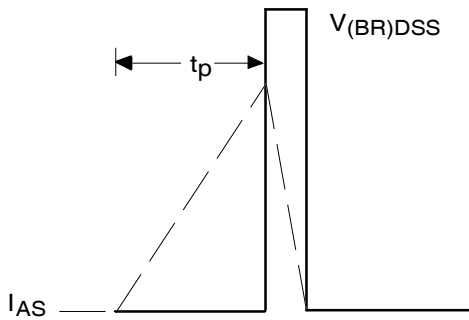


Fig 12b. Unclamped Inductive Waveforms

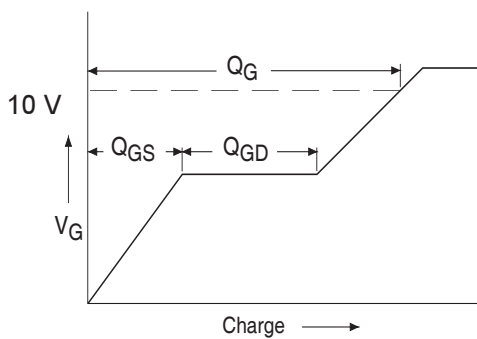


Fig 13a. Basic Gate Charge Waveform

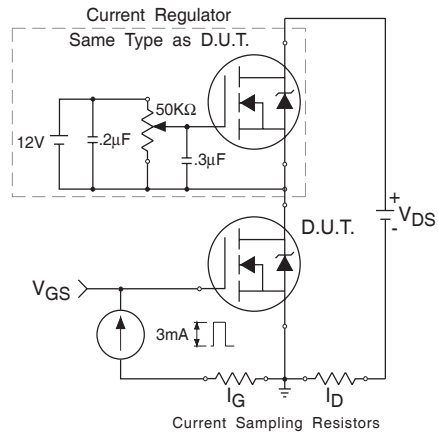
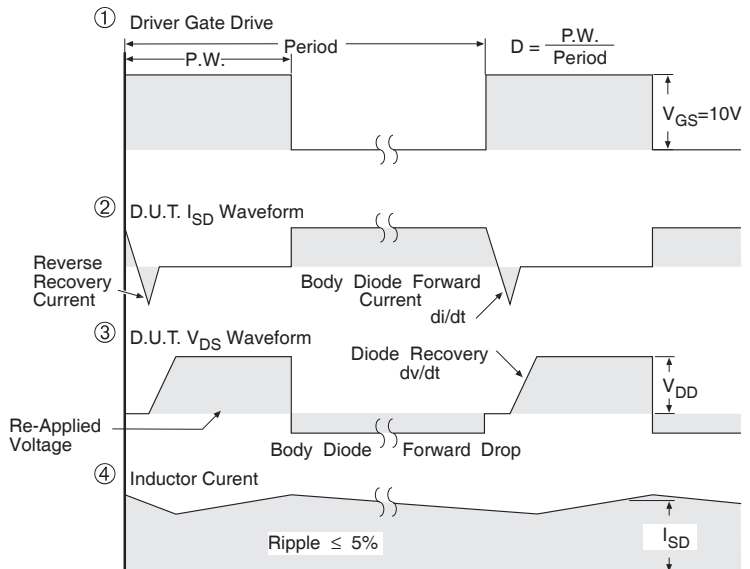
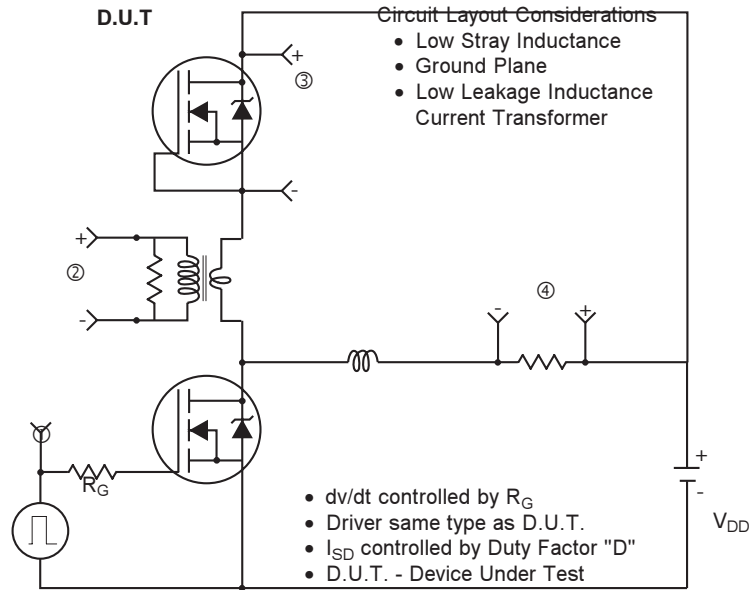


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



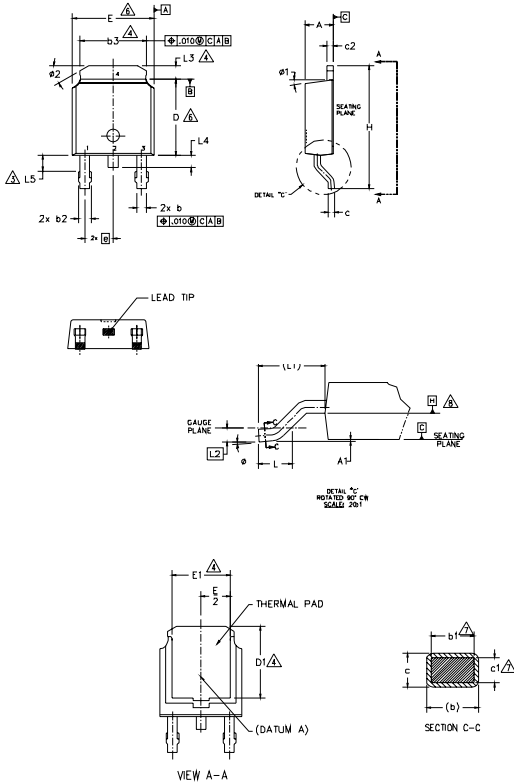
\*  $V_{GS} = 5V$  for Logic Level Devices

Fig 14. For N-Channel HEXFETS



## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
  - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
  - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.1 [0.13 AND 0.25] FROM THE LEAD TIP.
  - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
  - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

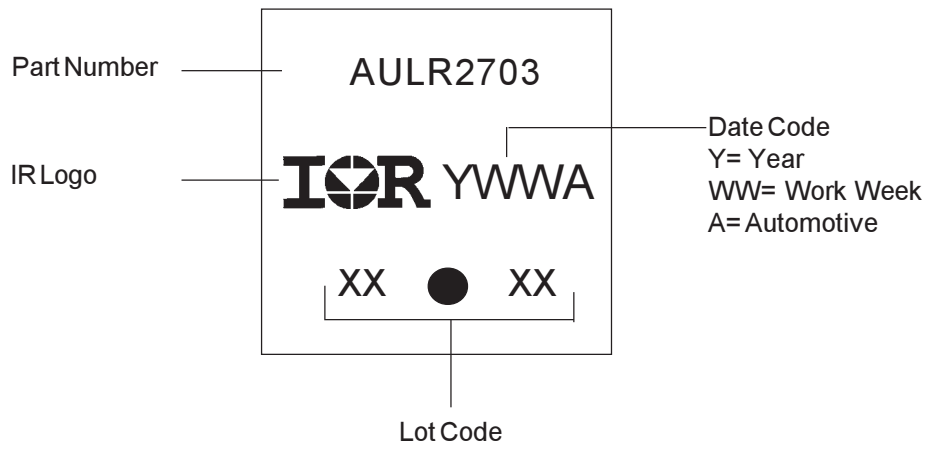
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

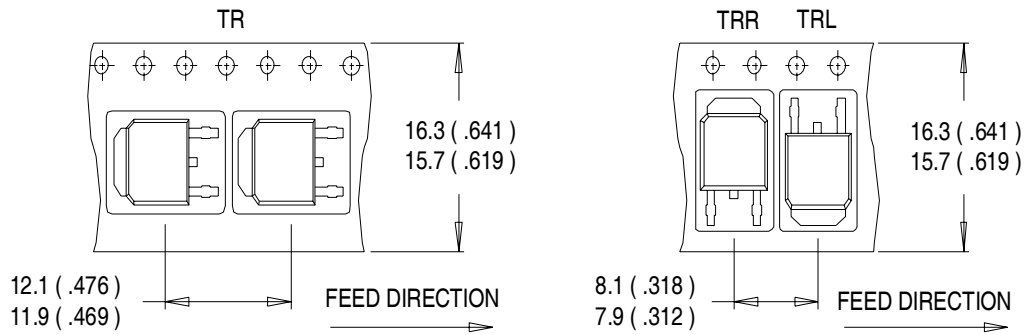
## D-Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

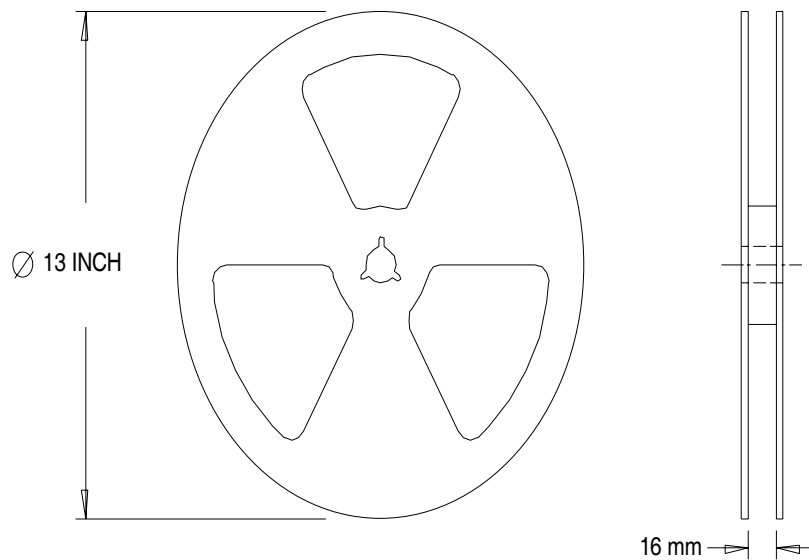
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



### NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLR2703	Dpak	Tube	75	AUIRLR2703
		Tape and Reel	2000	AUIRLR2703TR
		Tape and Reel Left	3000	AUIRLR2703TRL
		Tape and Reel Right	3000	AUIRLR2703TRR